

Supporting Information

355 nm Nanosecond Ultraviolet Pulsed Laser Annealing Effects on Amorphous In-Ga-ZnO Thin Film Transistors

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Supplementary Figures

(A) ITO Sputtering



(B) Photolithography(for Lift-off)



(C) a-IGZO Sputtering



(D) Lift-off



Figure S1. Fabrication process of an a-IGZO/ITO TFT (a) ITO sputtering and patterning (b) photolithography for lift-off (c) a-IGZO sputtering (d) Lift-off

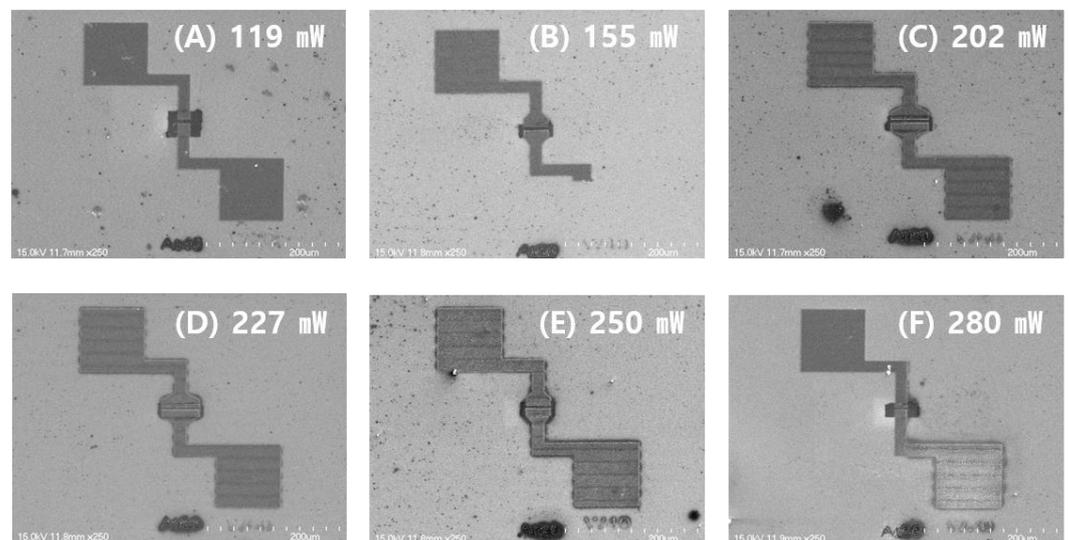


Figure S2. SEM images of a-IGZO TFTs after a 35 nm UV pulsed laser annealing process for laser beam energies of (a) 119 mW, (b) 155 mW, (c) 202 mW, (d) 227 mW, (e) 250 mW, and (f) 280 mW